

SANYO Semiconductors DATA SHEET



N-Channel Silicon MOSFET 2SK4098FG — General-Purpose Switching Device **Applications**

Features

- · Low ON-resistance, low input capacitance, ultrahigh-speed switching.
- · Adoption of high reliability HVP process.
- · Attachment workability is good by Mica-less package.
- Avalanche resistance guarantee.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		600	V
Gate-to-Source Voltage	VGSS		±30	V
Drain Current (DC)	I _{Dc} *1	Limited only by maximum temperature Tch=150°C	7	А
	IDpack *2	Tc=25°C (SANYO's ideal heat dissipation condition)*3	6	А
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	28	А
Allowable Power Dissipation	De		2.0	W
	PD	Tc=25°C (SANYO's ideal heat dissipation condition)*3	33	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *4	EAS		98	mJ
Avalanche Current *5	IAV		6	А

Note :*1 Shows chip capability.

*2 Package limited.

*3 SANYO's condition is radiation from backside.

The method is applying silicone grease to the backside of the device and attaching the device to water-cooled radiator made of aluminium.

*4 VDD=50V, L=5mH, IAV=6A

*5 L≤5mH, Single pulse

Marking: K4098

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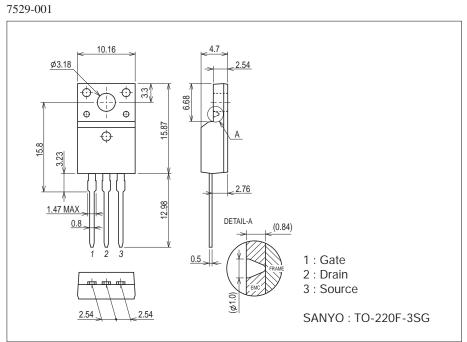
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Electrical Characteristics at Ta=25°C

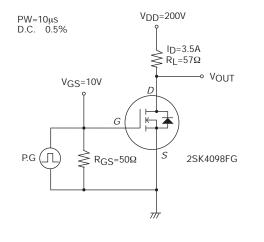
Parameter	Symbol	Conditions	Ratings			11-14
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=10mA, VGS=0V	600			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =480V, V _{GS} =0V			100	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =±30V, V _{DS} =0V			±100	nA
Cutoff Voltage	V _{GS} (off)	V _{DS} =10V, I _D =1mA	3		5	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =3.5A	2.1	4.2		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)	ID=3.5A, VGS=10V		0.9	1.1	Ω
Input Capacitance	Ciss	V _{DS} =30V, f=1MHz		600		pF
Output Capacitance	Coss	V _{DS} =30V, f=1MHz		120		pF
Reverse Transfer Capacitance	Crss	VDS=30V, f=1MHz		25		рF
Turn-ON Delay Time	t _d (on)	See specified Test Circuit.		17		ns
Rise Time	tr	See specified Test Circuit.		34		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		80		ns
Fall Time	tf	See specified Test Circuit.		30		ns
Total Gate Charge	Qg	VDS=200V, VGS=10V, ID=7A		23.5		nC
Gate-to-Source Charge	Qgs	V _{DS} =200V, V _{GS} =10V, I _D =7A		4.5		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =200V, V _{GS} =10V, I _D =7A		13.5		nC
Diode Forward Voltage	V _{SD}	IS=7A, VGS=0V		0.9	1.2	V

Package Dimensions

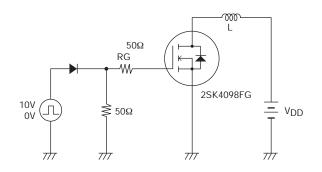
unit : mm (typ)



Switching Time Test Circuit



Avalanche Resistance Test Circuit



2SK4098FG

For this package, a part of inner electrode is exposed. Please refer to the package outline for the detailedstructure.

So when mounting the device, please pay enough attention to the isolation with the heatsink.

According to the device mounting method, sometimes the insulation voltage may be decreased. (refer to the below insulation characteristics)

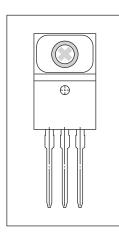
Insulation / Ta=25°C / RH75%

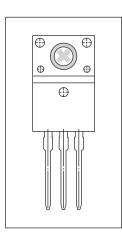
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Lead & resin insulation *	VISO1	Metal spacer Refer to Fig.1		1600		Vrms
	VISO2	Washer 5.8mm Refer to Fig.2		2100		Vrms
	VISO3	Insulated screw, Insulated washer		3900		Vrms

*: AC voltage measurement

Fig.1

Fig.2

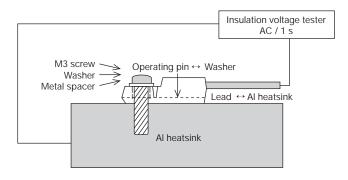




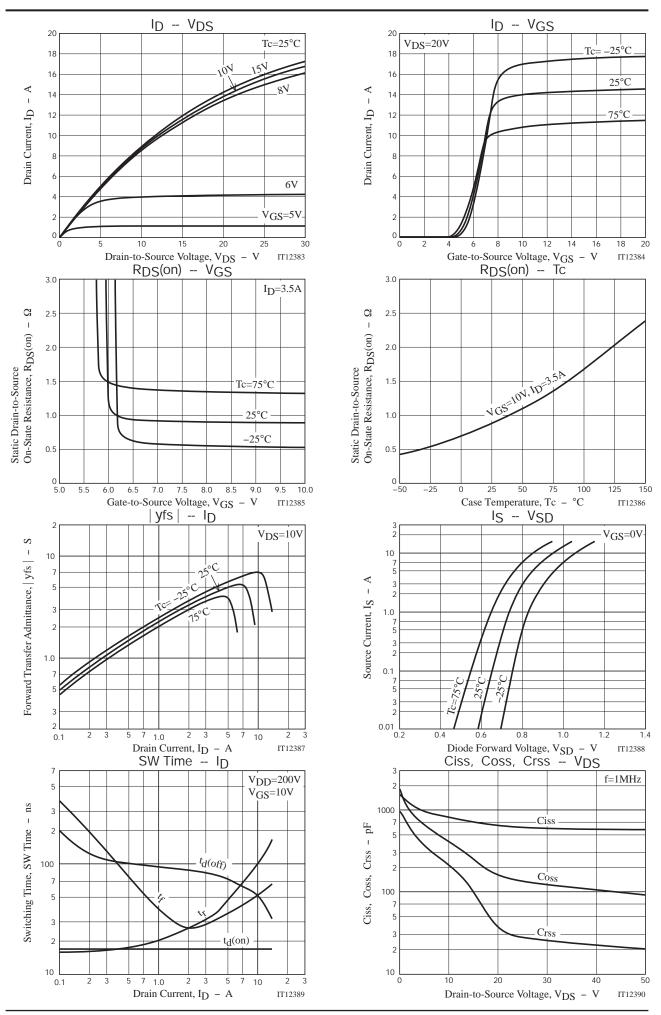
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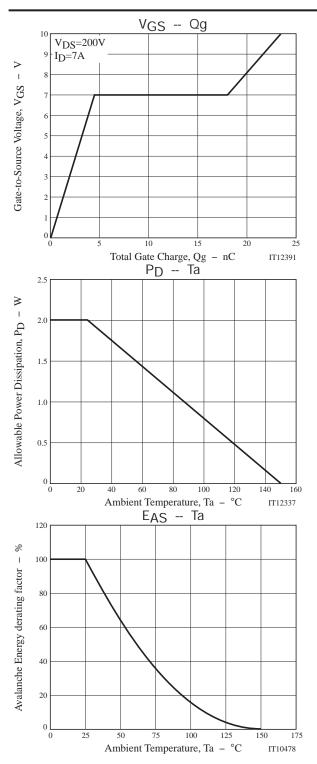
Insulation Measuring Diagram

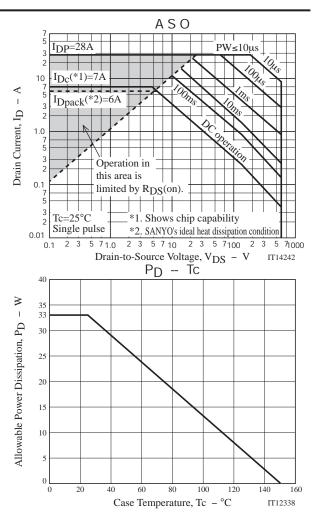


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No. A1364-4/6





Note on usage : Since the 2SK4098FG is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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